

## N-channel 30 V 2.1 m $\Omega$ logic level MOSFET in D2PAK

Rev. 1 — 20 March 2012

Product data sheet

#### **Product profile** 1.

#### **1.1 General description**

Logic level N-channel MOSFET in D2PAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

#### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for logic level gate drive sources

#### **1.3 Applications**

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

#### 1.4 Quick reference data

Table 1.	Quick reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	30	V
I <sub>D</sub>	drain current	$T_{mb}$ = 25 °C; $V_{GS}$ = 10 V; see <u>Figure 1</u>	[1]	-	-	100	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	-	211	W
Tj	junction temperature			-55	-	175	°C
Static cha	aracteristics						
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 100 °C; see <u>Figure 12</u> ; see <u>Figure 11</u>		-	2.51	2.9	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; see <u>Figure 11</u>		-	1.79	2.1	mΩ
Dynamic	characteristics						
Q <sub>GD</sub>	gate-drain charge	$V_{GS}$ = 4.5 V; $I_{D}$ = 25 A; $V_{DS}$ = 15 V;		-	16	-	nC
Q <sub>G(tot)</sub>	total gate charge	see Figure 13; see Figure 14		-	55	-	nC
Avalanch	e ruggedness						
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 100 A; $V_{sup} \le$ 30 V; $R_{GS}$ = 50 $\Omega$ ; unclamped		-	-	555	mJ

[1] Continuous current is limited by package.

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#### N-channel 30 V 2.1 m $\Omega$ logic level MOSFET in D2PAK

#### 2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain <sup>[1]</sup>	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

[1] It is not possible to make connection to pin 2

#### 3. Ordering information

# Table 3. Ordering information Type number Package Name Description Version PSMN2R0-30BL D2PAK plastic single-ended surface-mounted package (D2PAK); 3 leads SOT404 (one lead cropped)

#### 4. Marking

Table 4.   Marking codes	
Type number	Marking code
PSMN2R0-30BL	PSMN2R0-30BL

N-channel 30 V 2.1 m $\Omega$  logic level MOSFET in D2PAK

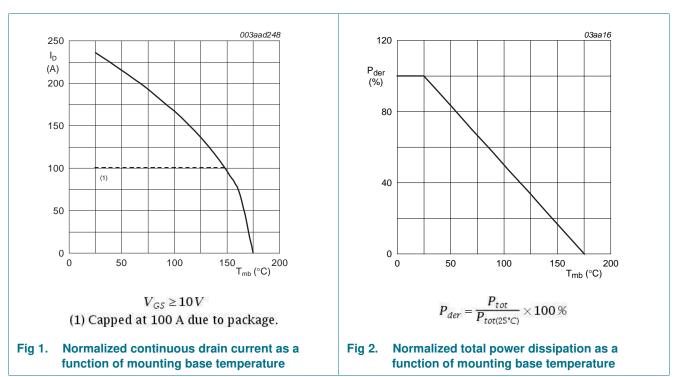
#### 5. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

	_					
Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	30	V
V <sub>DGR</sub>	drain-gate voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C; R <sub>GS</sub> = 20 kΩ		-	30	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	$V_{GS}$ = 10 V; $T_{mb}$ = 100 °C; see <u>Figure 1</u>	<u>[1]</u>	-	100	А
		$V_{GS}$ = 10 V; $T_{mb}$ = 25 °C; see <u>Figure 1</u>	<u>[1]</u>	-	100	А
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$ ; see Figure 3		-	943	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	211	W
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature			-	260	°C
Source-dr	ain diode					
ls	source current	T <sub>mb</sub> = 25 °C	<u>[1]</u>	-	100	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	943	А
Avalanche	ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 100 A; $V_{sup}$ ≤ 30 V; $R_{GS}$ = 50 Ω; unclamped		-	555	mJ

[1] Continuous current is limited by package.



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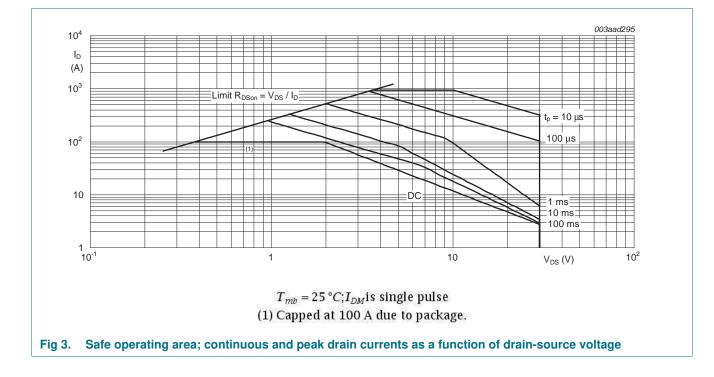


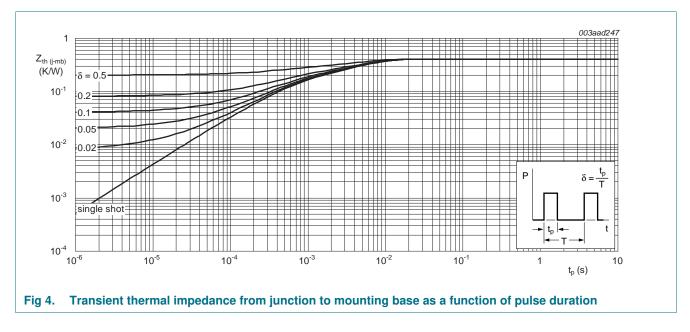
Table C

#### N-channel 30 V 2.1 mΩ logic level MOSFET in D2PAK

#### **Thermal characteristics** 6.

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Table 6.	Inermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.41	0.71	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	maximum foot print; mounted on a printed circuit board	-	50	-	K/W



N-channel 30 V 2.1 mΩ logic level MOSFET in D2PAK

#### 7. Characteristics

#### Table 7. Characteristics

Tested to JEDEC standards where applicable.

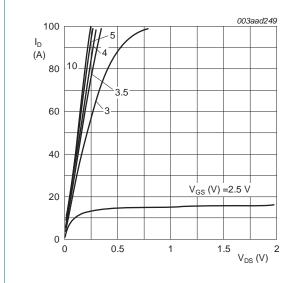
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$	30	-	-	V
		$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^{\circ}C$	27	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 9</u> ; see <u>Figure 10</u>	1.3	1.7	2.15	V
		$\label{eq:ID} \begin{split} I_D = 1 \mbox{ mA; } V_{DS} = V_{GS};  T_j = 175 \mbox{ °C}; \\ see \mbox{ Figure 10} \end{split}$	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see <u>Figure 10</u>	-	-	2.45	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	3	μA
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$	-	-	70	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
		$V_{GS} = -16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
R <sub>DSon</sub> drain-source on-state resistance	drain-source on-state resistance	$V_{GS}$ = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; see <u>Figure 11</u>	-	2.47	2.9	mΩ
		$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 175 °C; see <u>Figure 12</u> ; see <u>Figure 11</u>	-	3.4	4	mΩ
	$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 100 °C; see <u>Figure 12</u> ; see <u>Figure 11</u>	-	2.51	2.9	mΩ	
	$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 25 °C; see <u>Figure 11</u>	-	1.79	2.1	mΩ	
R <sub>G</sub>	gate resistance	f = 1 MHz	-	0.78	-	Ω
Dynamic o	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	107	-	nC
		$I_D$ = 25 A; $V_{DS}$ = 15 V; $V_{GS}$ = 10 V; see <u>Figure 13</u> ; see <u>Figure 14</u>	-	117	-	nC
		$I_D = 25 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$	-	55	-	nC
Q <sub>GS</sub>	gate-source charge	see Figure 13; see Figure 14	-	17	-	nC
$\sim$						nC
GS(th)	pre-threshold gate-source charge		-	11	-	no
	pre-threshold gate-source charge post-threshold gate-source charge		-	11 6	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source				-	
Q <sub>GS(th-pl)</sub> Q <sub>GD</sub>	post-threshold gate-source charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 25 V; see <u>Figure 13</u> ; see <u>Figure 14</u>	- - -	6	- - -	nC
Q <sub>GS(th-pl)</sub> Q <sub>GD</sub> V <sub>GS(pl)</sub>	post-threshold gate-source charge gate-drain charge			6 16	- - - -	nC nC
Q <sub>GS(th-pl)</sub> Q <sub>GD</sub> V <sub>GS(pl)</sub> C <sub>iss</sub>	post-threshold gate-source charge gate-drain charge gate-source plateau voltage	see Figure 14		6 16 2.6	-	nC nC V
Q <sub>GS</sub> (th-pl) Q <sub>GD</sub> V <sub>GS</sub> (pl) C <sub>iss</sub> C <sub>oss</sub>	post-threshold gate-source charge gate-drain charge gate-source plateau voltage input capacitance	see <u>Figure 14</u> V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 0 V; f = 1 MHz;	- - - - -	6 16 2.6 6810	- - -	nC nC V pF
Q <sub>GS</sub> (th-pl) Q <sub>GD</sub> V <sub>GS</sub> (pl) C <sub>iss</sub> C <sub>oss</sub> C <sub>rss</sub>	post-threshold gate-source charge gate-drain charge gate-source plateau voltage input capacitance output capacitance	see <u>Figure 14</u> V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 0 V; f = 1 MHz;	- - - - - - - -	6 16 2.6 6810 1410		nC nC V pF pF
Q <sub>GS</sub> (th-pl) Q <sub>GD</sub> V <sub>GS</sub> (pl) C <sub>iss</sub> C <sub>oss</sub> C <sub>rss</sub>	post-threshold gate-source charge gate-drain charge gate-source plateau voltage input capacitance output capacitance reverse transfer capacitance	see Figure 14 $V_{DS} = 15 \text{ V}; \text{ V}_{GS} = 0 \text{ V}; \text{ f} = 1 \text{ MHz};$ $T_j = 25 \text{ °C}; \text{ see Figure 15}$	- - - - - - - - - - -	6 16 2.6 6810 1410 650	- - - -	nC NC V pF pF
Q <sub>GS</sub> (th) Q <sub>GS</sub> (th-pl) Q <sub>GD</sub> V <sub>GS</sub> (pl) C <sub>iss</sub> C <sub>oss</sub> C <sub>rss</sub> t <sub>d</sub> (on) t <sub>r</sub> t <sub>d</sub> (off)	post-threshold gate-source charge gate-drain charge gate-source plateau voltage input capacitance output capacitance reverse transfer capacitance turn-on delay time	see Figure 14 $V_{DS} = 15 V; V_{GS} = 0 V; f = 1 MHz;$ $T_j = 25 \text{ °C}; \text{ see Figure 15}$ $V_{DS} = 15 V; R_L = 0.5 \Omega; V_{GS} = 4.5 V;$	- - - - - - - - - - - - - - -	6 16 2.6 6810 1410 650 63	- - - - -	nC nC V pF pF pF ns

#### N-channel 30 V 2.1 m $\Omega$ logic level MOSFET in D2PAK

#### Table 7. Characteristics ...continued

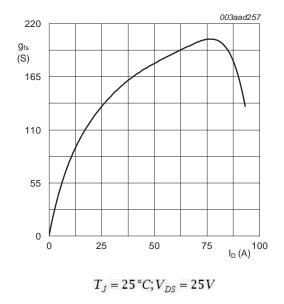
Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Source-dr	ain diode					
$V_{SD}$	source-drain voltage	I <sub>S</sub> = 25 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; see <u>Figure 16</u>	-	0.76	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_{S} = 25 \text{ A}; \text{ d}I_{S}/\text{d}t = -100 \text{ A}/\mu\text{s};$	-	49	-	ns
Qr	recovered charge	$V_{GS} = 0 V; V_{DS} = 15 V$	-	66	-	nC

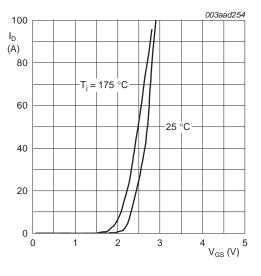


 $T_j = 25 \,^{\circ}C$ 



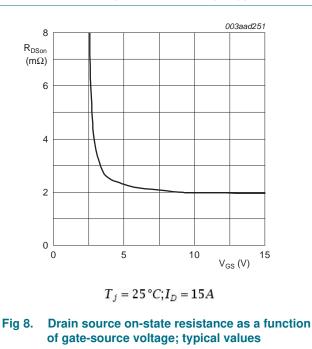




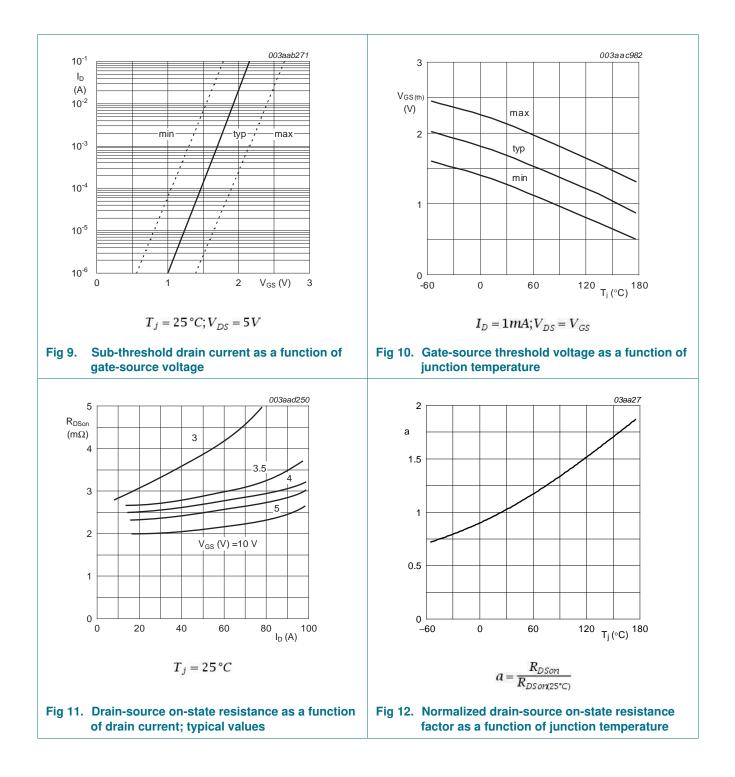




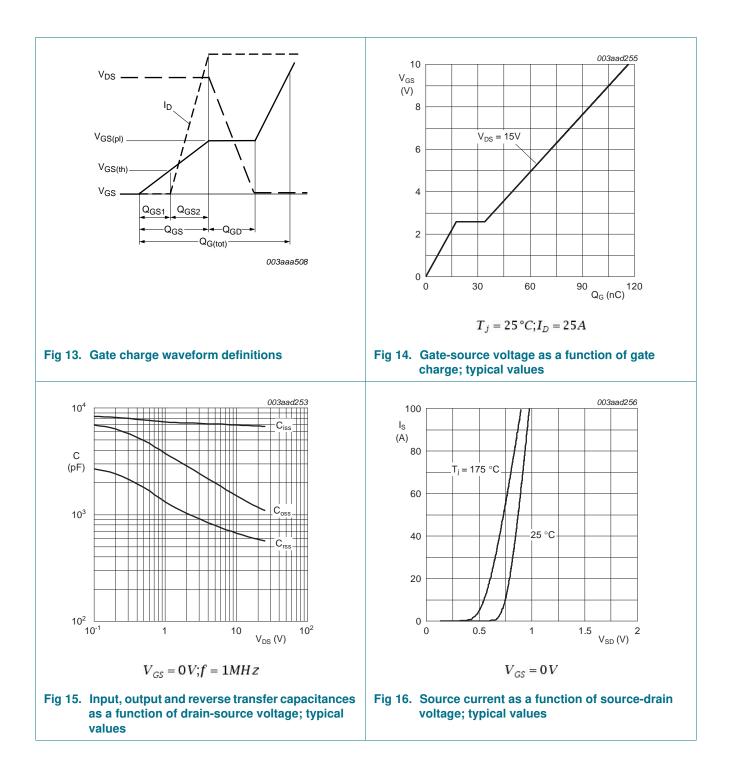




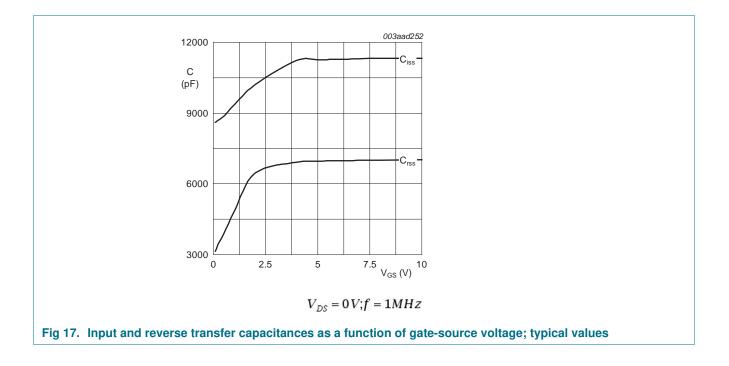
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# PSMN2R0-30BL

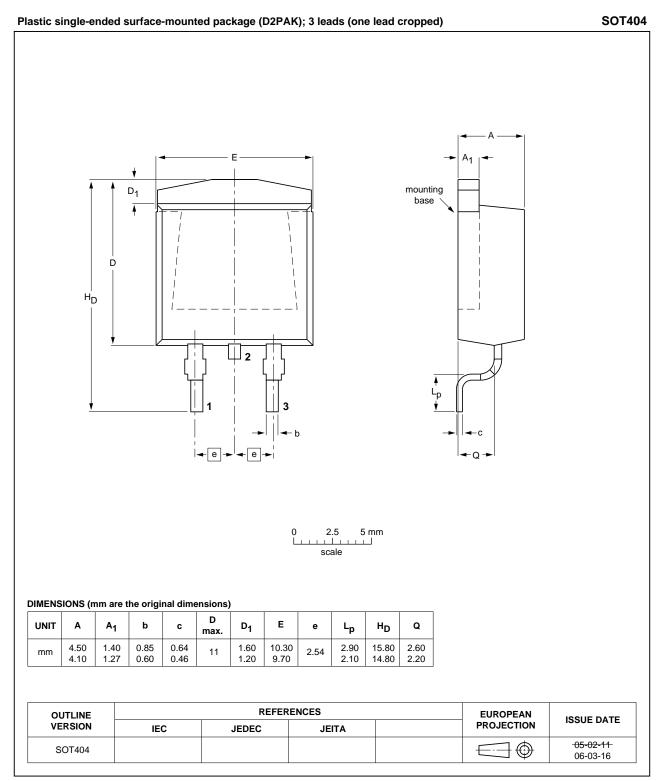


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#### N-channel 30 V 2.1 m $\Omega$ logic level MOSFET in D2PAK

#### 8. Package outline



#### Fig 18. Package outline SOT404 (D2PAK)

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PSMN2R0-30BL

#### N-channel 30 V 2.1 mΩ logic level MOSFET in D2PAK

### 9. Revision history

Table 8. Revision h	Revision history						
Document ID	Release date	Data sheet status	Change notice	Supersedes			
PSMN2R0-30BL v.1	20120320	Product data sheet	-	-			

#### N-channel 30 V 2.1 mΩ logic level MOSFET in D2PAK

#### **10. Legal information**

#### **10.1 Data sheet status**

Document status <sup>[1]</sup> [2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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